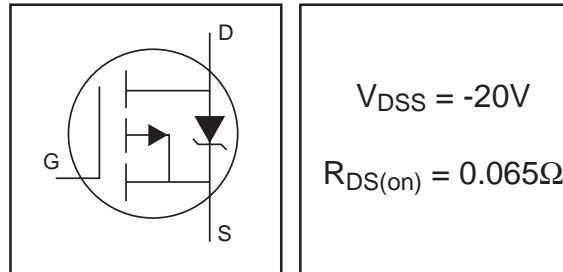


# IRLML6402

HEXFET® Power MOSFET

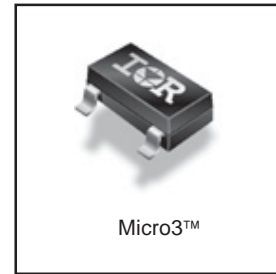
- Ultra Low On-Resistance
- P-Channel MOSFET
- SOT-23 Footprint
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching



## Description

These P-Channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET® power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in battery and load management.

A thermally enhanced large pad leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3™, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards. The thermal resistance and power dissipation are the best available.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain- Source Voltage	-20	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -4.5\text{V}$	-3.7	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -4.5\text{V}$	-2.2	
$I_{DM}$	Pulsed Drain Current ①	-22	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	1.3	W
$P_D @ T_A = 70^\circ\text{C}$	Power Dissipation	0.8	
	Linear Derating Factor	0.01	W/°C
$E_{AS}$	Single Pulse Avalanche Energy④	11	mJ
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	V
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

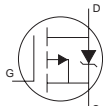
## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	75	100	°C/W

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	-0.009	—	V/°C	Reference to 25°C, I <sub>D</sub> = -1mA ②
R <sub>DSON</sub>	Static Drain-to-Source On-Resistance	—	0.050	0.065	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.7A ②
		—	0.080	0.135		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -3.1A ②
V <sub>GS(th)</sub>	Gate Threshold Voltage	-0.40	-0.55	-1.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
g <sub>fs</sub>	Forward Transconductance	6.0	—	—	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -3.7A ②
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	-1.0	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
		—	—	-25		V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 70°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	-100	nA	V <sub>GS</sub> = -12V
	Gate-to-Source Reverse Leakage	—	—	100		V <sub>GS</sub> = 12V
Q <sub>g</sub>	Total Gate Charge	—	8.0	12	nC	I <sub>D</sub> = -3.7A
Q <sub>gs</sub>	Gate-to-Source Charge	—	1.2	1.8		V <sub>DS</sub> = -10V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	2.8	4.2		V <sub>GS</sub> = -5.0V ②
t <sub>d(on)</sub>	Turn-On Delay Time	—	350	—	ns	V <sub>DD</sub> = -10V
t <sub>r</sub>	Rise Time	—	48	—		I <sub>D</sub> = -3.7A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	588	—		R <sub>G</sub> = 89Ω
t <sub>f</sub>	Fall Time	—	381	—		R <sub>D</sub> = 2.7Ω
C <sub>iss</sub>	Input Capacitance	—	633	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	145	—		V <sub>DS</sub> = -10V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	110	—		f = 1.0MHz

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	-1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	-22		
V <sub>SD</sub>	Diode Forward Voltage	—	—	-1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = -1.0A, V <sub>GS</sub> = 0V ②
t <sub>rr</sub>	Reverse Recovery Time	—	29	43	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = -1.0A
Q <sub>rr</sub>	Reverse Recovery Charge	—	11	17	nC	di/dt = -100A/μs ②

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ③ Surface mounted on 1" square single layer 1oz. copper FR4 board, steady state.
- ④ Starting T<sub>J</sub> = 25°C, L = 1.65mH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = -3.7A.

\*\* For recommended footprint and soldering techniques refer to application note #AN-994.

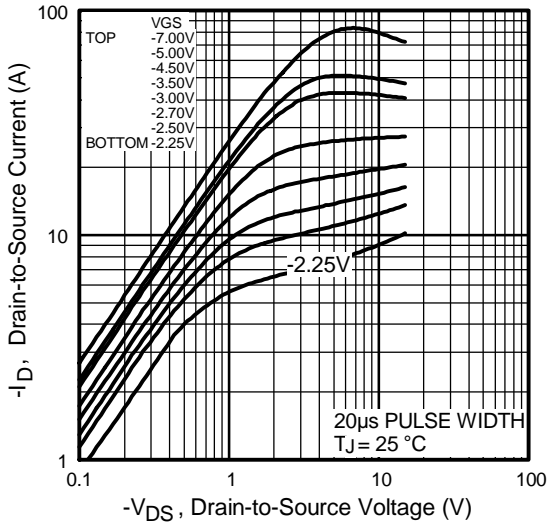


Fig 1. Typical Output Characteristics

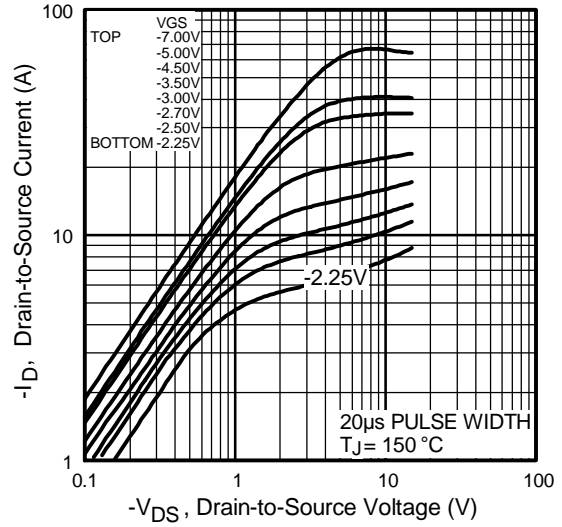


Fig 2. Typical Output Characteristics

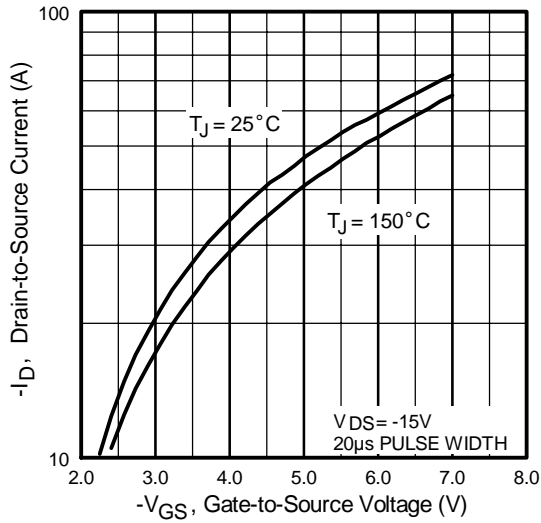


Fig 3. Typical Transfer Characteristics

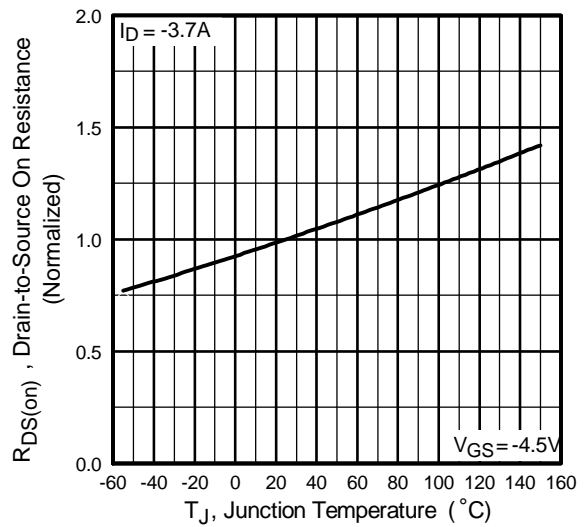
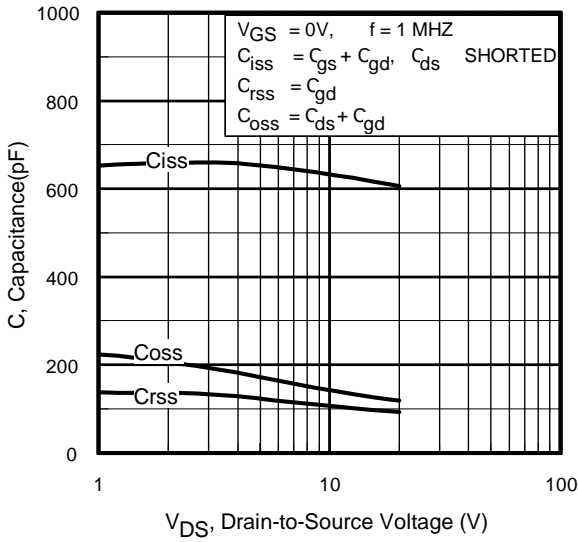
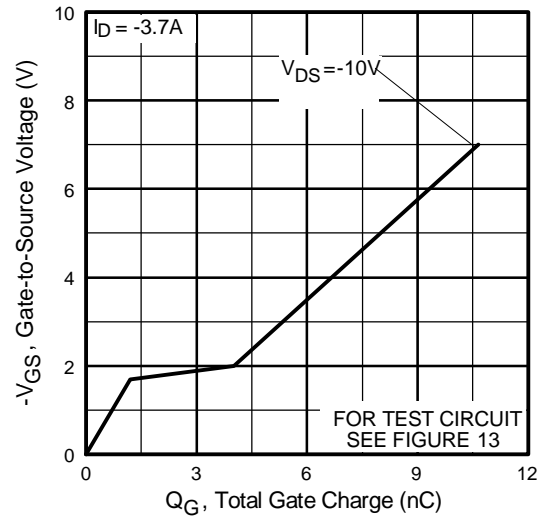


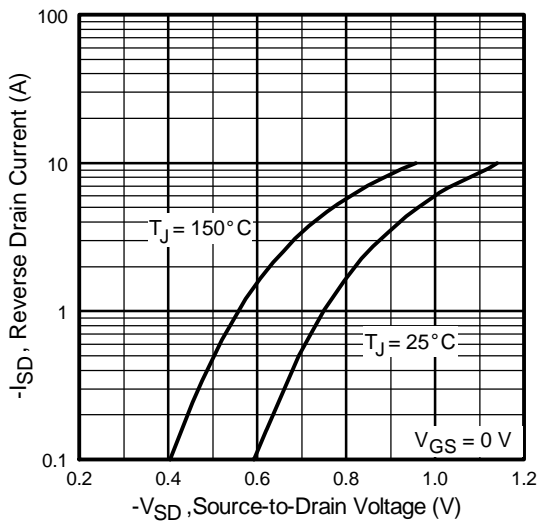
Fig 4. Normalized On-Resistance Vs. Temperature



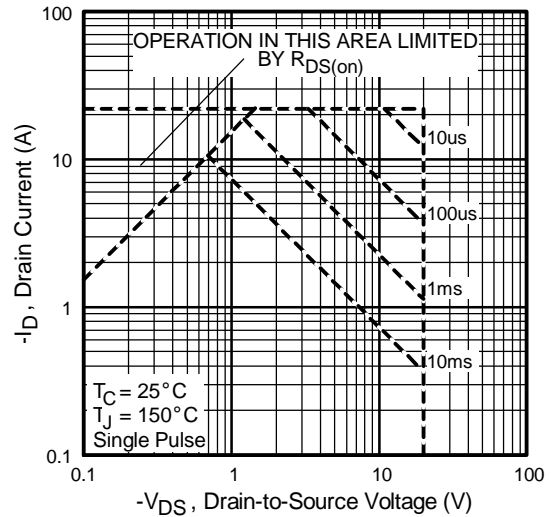
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



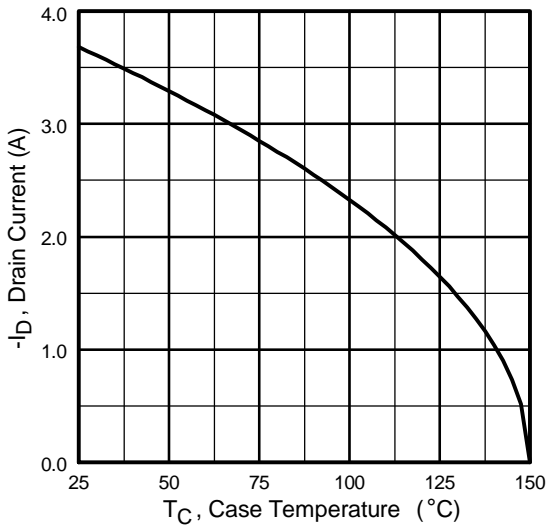
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



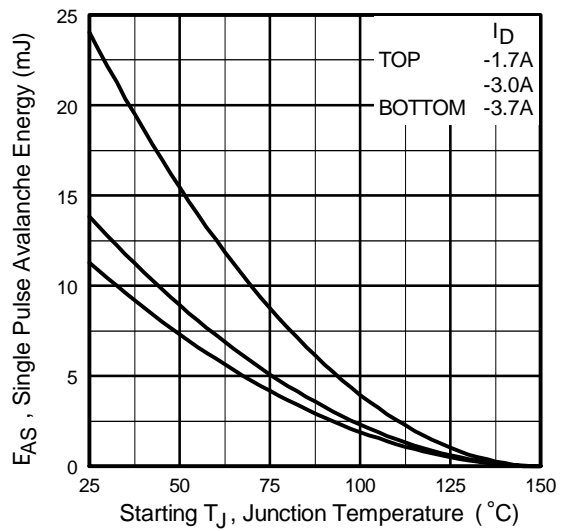
**Fig 7.** Typical Source-Drain Diode Forward Voltage



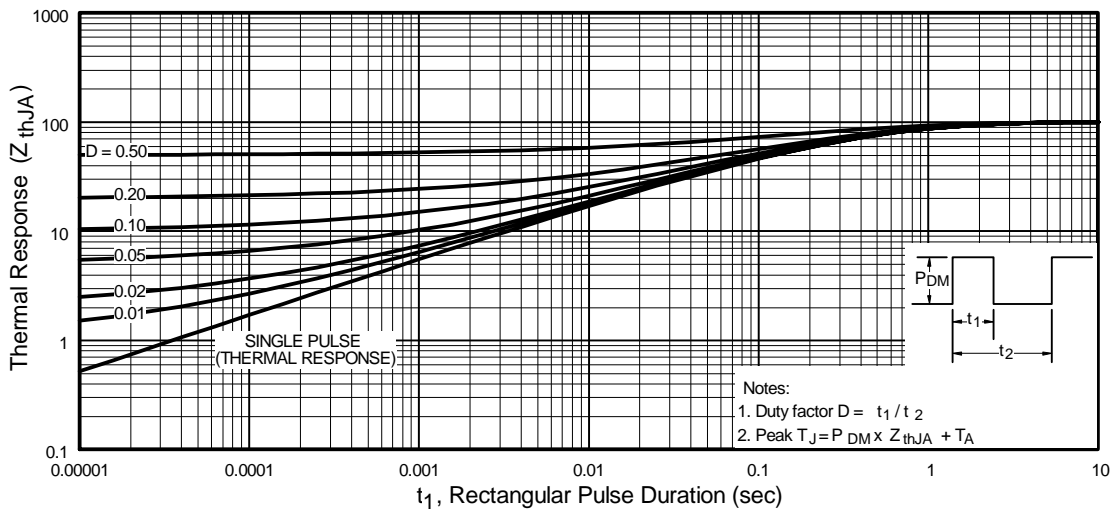
**Fig 8.** Maximum Safe Operating Area



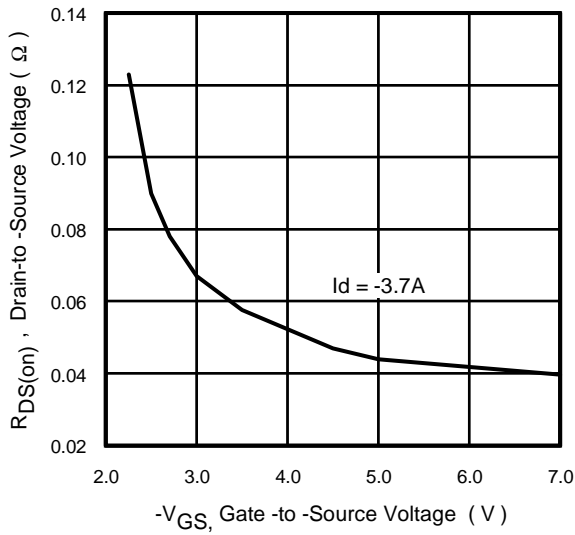
**Fig 9.** Maximum Drain Current Vs. Case Temperature



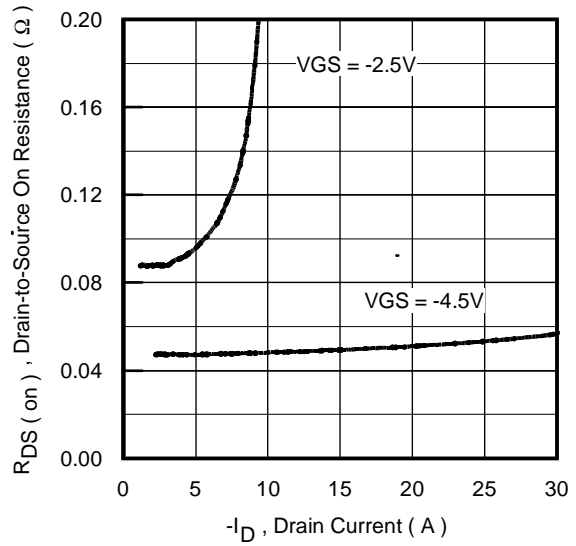
**Fig 10.** Maximum Avalanche Energy Vs. Drain Current



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



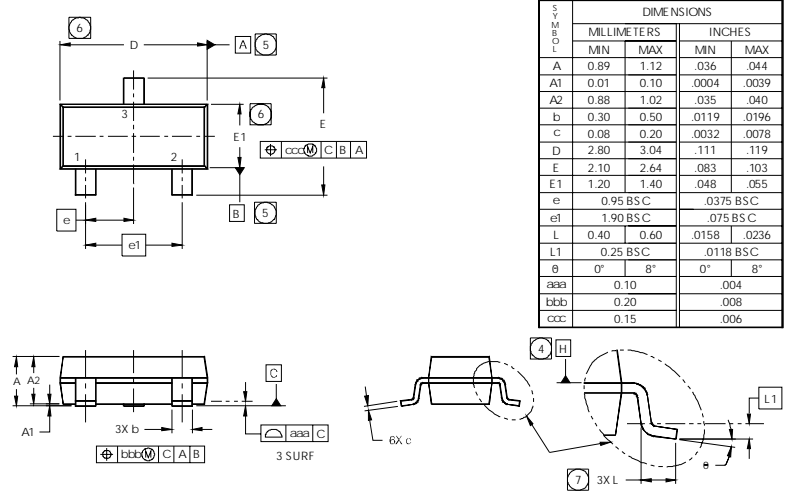
**Fig 12.** Typical On-Resistance Vs. Gate Voltage



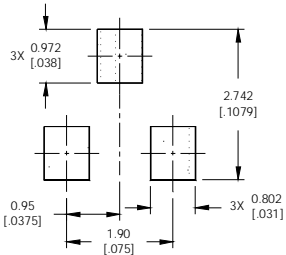
**Fig 13.** Typical On-Resistance Vs. Drain Current

## Micro3 (SOT-23/TO-263AB) Package Outline

Dimensions are shown in millimeters (inches)

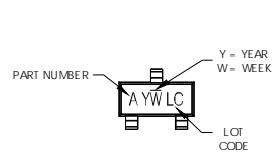


### RECOMMENDED FOOTPRINT



- NOTES
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS AND INCHES.
  3. CONTROLLING DIMENSION: MILLIMETER.
  4. DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE.
  5. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
  6. DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H.
  7. DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
  8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-236AB.

## Micro3 (SOT-23/TO-236AB) Part Marking Information



- PART NUMBER CODE REFERENCE:
- A = IRLML2402
  - B = IRLML2803
  - C = IRLML6302
  - D = IRLML5103
  - E = IRLML6402
  - F = IRLML6401
  - G = IRLML2502
  - H = IRLML5203
- Note: A line above the work week (as shown here) indicates Lead-Free.

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
1994	4	04	D
1995	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

W = (27-52) IF PRECEDED BY A LETTER

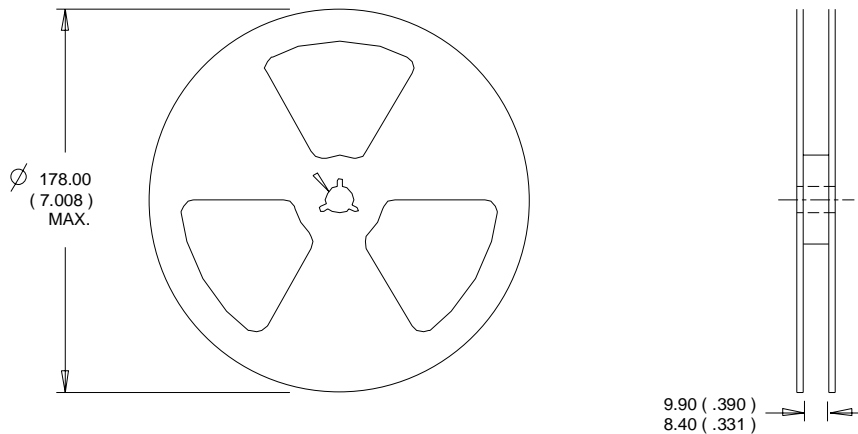
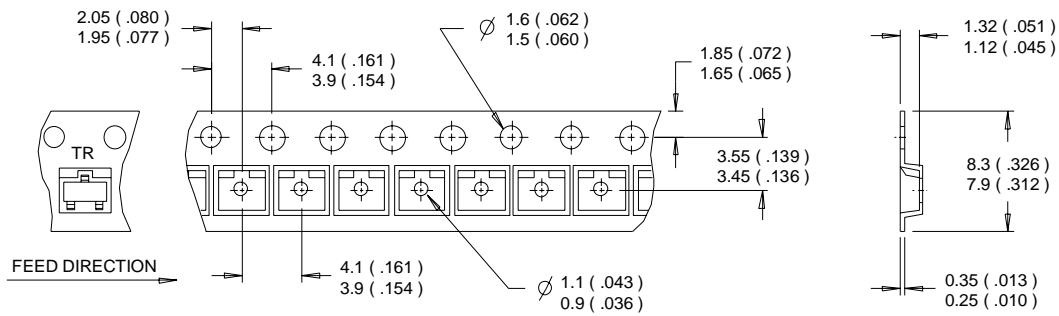
YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
1994	D	30	D
1995	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

# IRLML6402

International  
**IR** Rectifier

## Micro3™(SOT-23/TO-263AB) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.

International  
**IR** Rectifier

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